

CMC Teleconference: February 9, 2005

Attendees:

Philips, TI, IBM, Freescale, Renesas, Hiroshima University, Technical University of Crete, Penn State University, RFMD

We reviewed the action items from the previous phone meeting January 19, 2005

IBM will provide the Lpoly offset for the RF DUTs. Complete

IBM will check the correctness of the PMOS 0.12/1 DC I-V data at -55C. Complete. All of the PMOS, -55C, W=.12, IdVd data was not adjusted for multiplicity. IBM will correct the data and send to Keith to place on the website. IBM also noted that the IdVg and IdVd data for the W=.12/L=.1, T=-55C data showed a few percent delta for the same bias conditions. Since this was one of the points we intended to make plots for it was decided to use a different device. We selected W=.16/L=.08.

After the meeting IBM determined that there was no T=-55 for this size. The W=.12/L=.16 device will be used.

IBM will see if changes in key parameters (VT, mobility, etc.) due to stress can be provided for the RF DUTs. Complete, provided.

Colin McAndrew (Freescale) will send out a Perl script with y parameter transformations that can be used as a reference and help ensure consistent transformations are used by everyone. Keith Green (TI) will post this on the CMC website. Complete

Keith will eliminate items 19-24 of the phase II deliverables document. Complete

Colin will send Joachim's email to Keith and he will post this on the CMC website. Complete

There was discussion of the S-parameter information IBM had provide and IBM answered questions.

It was agreed that all of the deliverables information would be consolidated into one deliverables document including decisions currently recorded in meeting minutes and the additional documents that have been posted to the web.

Action Item:

Matthias Bucher of TU Crete will provide a word document version of the PowerPoint file from Joachim Assenmacher. Keith Green will collect all the deliverables information into a single document.

We discussed the bias conditions for S-parameter comparison plots. We had previously decided to include only three gate biases ( $V_g = .2, .6, 1.0$ ). We will use these and three drain biases ( $V_d = .1, .6$  and  $1.2$ ). This is a change from the deliverables document which specifies  $.1$  and  $1.0$  volts for some tests and does not specify  $V_{drain}$  for others.

Action Item

Keith will include the above bias conditions when he updates the deliverables document.

Action Item

IBM will supply information on the area of the gate poly over STI for the three gate length structures measured for  $C_{gg}$ .

Action Item

Teams will review the parasitic parameters provided for the S-parameters and decide if they think something needs to be changed. If so they will inform Joe Watts ([jswatts@us.ibm.com](mailto:jswatts@us.ibm.com)) by February 18 and Joe will call another phone meeting.

This meeting was conducted in accordance with the EIA Legal Guides and EIA Manual of Organization and Procedure.